

IPA80R650CEXKSA2

IPA80R650CEXKSA2 Information



For Reference Only

Part Number IPA80R650CEXKSA2

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V TO-220-3

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPA80R650CEXKSA2 Specifications

Manufacturer Part Number IPA80R650CEXKSA2 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series CoolMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 8A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.9V @ 470μA Gate Charge (Qg) (Max) @ Vgs 45nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1100pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 33W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C8A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.9V @ 470μAGate Charge (Qg) (Max) @ Vgs45nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1100pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)33W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 5.1A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting Type-Supplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	Series	CoolMOS?
Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C8A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.9V @ 470μAGate Charge (Qg) (Max) @ Vgs45nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1100pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)33W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 5.1A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting Type-Supplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C BA (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature Au°C ~ 150°C (TJ) Mounting Type Supplier Device Package Package / Case 8A (Ta) 8	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.9V @ 470μAGate Charge (Qg) (Max) @ Vgs45nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1100pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)33W (Tc)Rds On (Max) @ Id, Vgs650 mOhm @ 5.1A, 10VOperating Temperature-40°C ~ 150°C (TJ)Mounting Type-Supplier Device PackageTO-220-3FPackage / CaseTO-220-3 Full Pack	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id 3.9V @ 470μA Gate Charge (Qg) (Max) @ Vgs 45nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1100pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 33W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Current - Continuous Drain (Id) @ 25°C	8A (Ta)
Gate Charge (Qg) (Max) @ Vgs 45nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1100pF @ 100V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 33W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Vgs(th) (Max) @ Id	3.9V @ 470μA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 33W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	45nC @ 10V
FET Feature - Power Dissipation (Max) 33W (Tc) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	1100pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 650 mOhm @ 5.1A, 10V Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	FET Feature	-
Operating Temperature -40°C ~ 150°C (TJ) Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	33W (Tc)
Mounting Type - Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	650 mOhm @ 5.1A, 10V
Supplier Device Package TO-220-3F Package / Case TO-220-3 Full Pack	Operating Temperature	-40°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	-
	Supplier Device Package	TO-220-3F
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

IPA80R650CEXKSA2 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPA80R650CEXKSA2 Payment Methods



















IPA80R650CEXKSA2 Shipping Methods













If you have any question about IPA80R650CEXKSA2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com